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P-Channel 40 V (D-S) MOSFEET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)			
- 40	0.0073 at V _{GS} = - 10 V	- 78 ^d			
	0.0095 at V _{GS} = - 4.5 V	- 70 ^d			

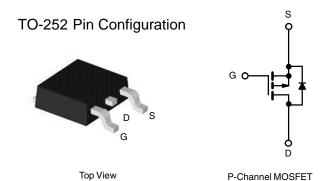
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualified for Automotive Applications



APPLICATIONS

- · Power Switch
- Load Switch in High Current Applications
- DC/DC Converters



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage		V_{DS}	- 40	V		
Gate-Source Voltage		V_{GS}	± 20	v		
Continuous Drain Current (T _{.I} = 175 °C)	T _C = 25 °C	ls.	- 78 ^d	A		
Continuous Brain Guilent (1) = 173 G)	T _C = 100 °C	I _D	- 63			
Pulsed Drain Current	I _{DM}	- 310	^			
Avalanche Current		I _{AR}			- 70	
Repetitive Avalanche Energy ^a	L = 0.1 mH	E _{AR}	155	mJ		
Power Dissipation	T _C = 25 °C	P _D	95 ^c	W		
Fower Dissipation	T _A = 25 °C	' D	3.3 ^{b, c}			
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient ^b	t ≤ 10 s	R _{thJA}	20	30	°C/W	
Junction-to-Ambient	Steady State		40	60		
Junction-to-Case		R _{thJC}		2.0		

Notes:

- a. Duty cycle \leq 1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.



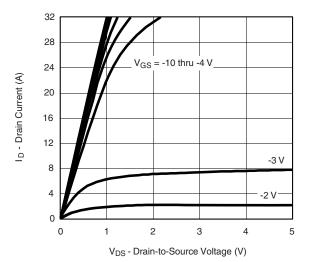
Parameter	Symbol	Symbol Test Conditions		Min. Typ.		Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 40			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	V _{GS} = ± 20 V		± 100	nA	
		V _{DS} = - 40 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 40 V, V _{GS} = 0 V, T _J = 125 °C		- 50		μΑ	
		V _{DS} = - 40 V, V _{GS} = 0 V, T _J = 150 °C			- 100		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 78			Α	
D : 0	D	V _{GS} = - 10 V, I _D = - 30 A		0.0073	0.009		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 20 A		0.0095	0.012	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 30 A		69		S	
Dynamic ^b							
Input Capacitance	C _{iss}			5580			
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = - 20 V, f = 1 MHz		570		pF	
Reverse Transfer Capacitance	C _{rss}]		60			
Total Gate Charge ^c	Qg	V _{DS} = - 20 V, V _{GS} = - 10 V, I _D = - 30 A	59				
				30		nC	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = -20 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -30 \text{ A}$		20			
Gate-Drain Charge ^c	Q_{gd}			7			
Gate Resistance	R _g	f = 1 MHz	1.8			Ω	
Turn-On Delay Time ^c	t _{d(on)}			15			
Rise Time ^c	t _r	$V_{DD} = -20 \text{ V}, R_L = 2 \Omega$		12		no	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong -30 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		70		- ns	
Fall Time ^c	t _f]		18			
Drain-Source Body Diode Ratings ar	nd Characteri	stics T _C = 25 °C ^b					
Continuous Current	I _S				- 78		
Pulsed Current	I _{SM}				- 310	Α	
Forward Voltage ^a	V _{SD}	I _F = - 10 A, V _{GS} = 0 V		- 0.8	- 1.5	V	
Reverse Recovery Time	t _{rr}			35	53	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = - 10 A, dI/dt = 100 A/μs		- 2	- 3	Α	
Reverse Recovery Charge	Q _{rr}			33	50	nC	

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

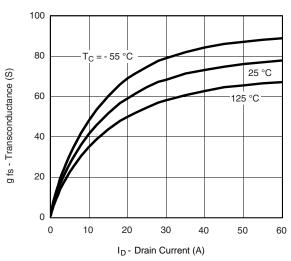
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



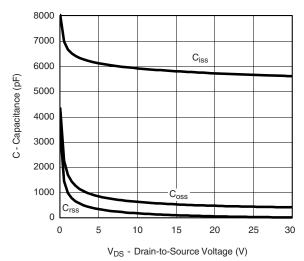
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



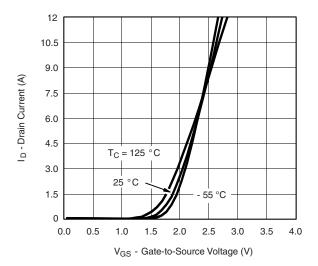
Output Characteristics



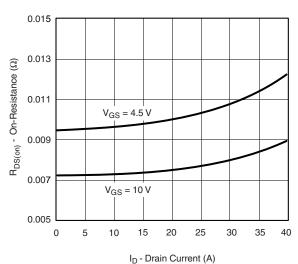
Transconductance



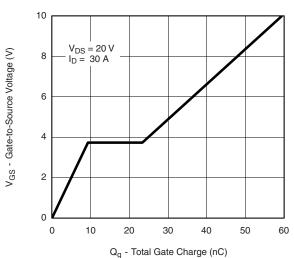
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current

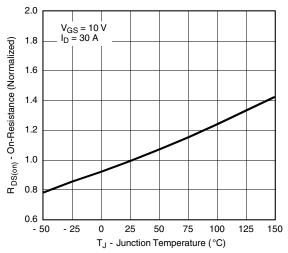


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TYPICAL CHARACTERISTICS

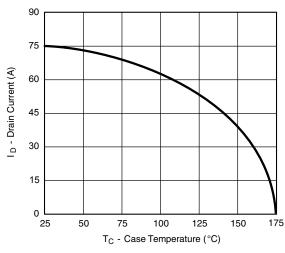


On-Resistance vs. Junction Temperature

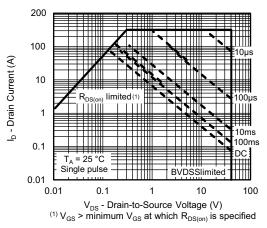
T_J = 150 °C T_J = 25 °C T_J = 25 °C V_{SD} - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

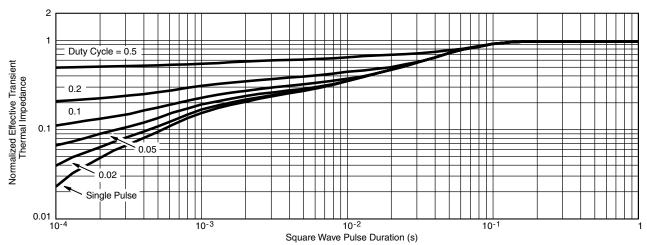
THERMAL RATINGS (25 °C, unless otherwise noted)



Drain Current vs. Case Temperature



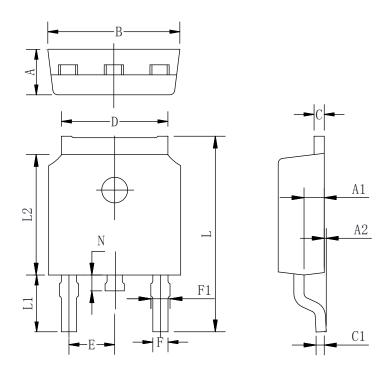
Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	
A	2.10	2.30	2.50	
A1	0.88	1.01	1.16	
A2	0.00	0.15	0.28	
В	6.40	6.60	6.80	
C	0.42	0.50	0.63	
C1	0.42	0.50	0.63	
D	5.08	5.32	5.65	
Е	2.286 TYP			
F	0.63	0.76	0.89	
F1	0.64	0.86	1.08	
L	9.30	9.90	10.80	
L1	2.4	2.8	3.6	
L2	5.90	6.10	6.55	
N	0.57	0.80	1.05	



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